

Welcome to [E-XFL.COM](https://www.e-xfl.com)

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	119
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/u1afs1500-fgg256i

Related Documents

Datasheet

Core8051

www.microsemi.com/soc/ipdocs/Core8051_DS.pdf

Application Notes

Fusion FlashROM

http://www.microsemi.com/soc/documents/Fusion_FROM_AN.pdf

Fusion SRAM/FIFO Blocks

http://www.microsemi.com/soc/documents/Fusion_RAM_FIFO_AN.pdf

Using DDR in Fusion Devices

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129938

Fusion Security

http://www.microsemi.com/soc/documents/Fusion_Security_AN.pdf

Using Fusion RAM as Multipliers

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129940

Handbook

Cortex-M1 Handbook

www.microsemi.com/soc/documents/CortexM1_HB.pdf

User Guides

Designer User Guide

http://www.microsemi.com/soc/documents/designer_UG.pdf

Fusion FPGA Fabric User Guide

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=130817

IGLOO, ProASIC3, SmartFusion and Fusion Macro Library Guide

http://www.microsemi.com/soc/documents/pa3_libguide_ug.pdf

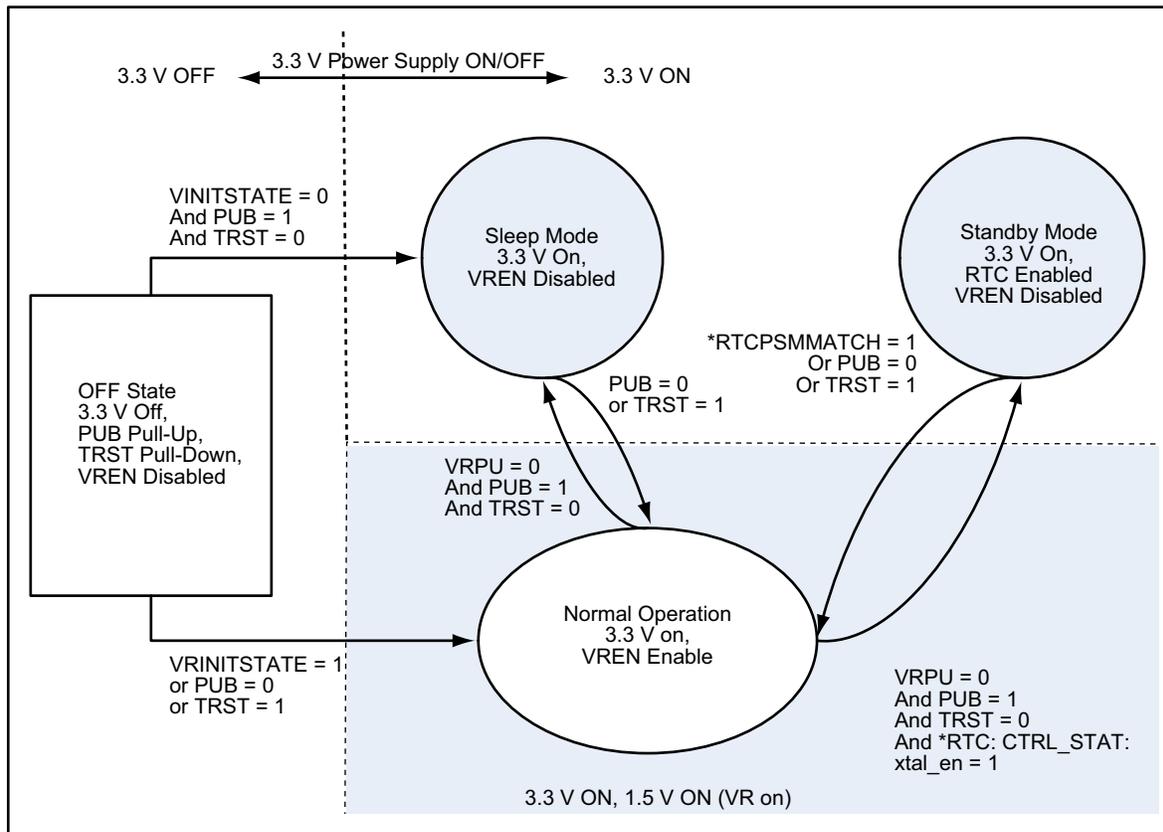
SmartGen, FlashROM, Flash Memory System Builder, and Analog System Builder User Guide

http://www.microsemi.com/soc/documents/genguide_ug.pdf

White Papers

Fusion Technology

http://www.microsemi.com/soc/documents/Fusion_Tech_WP.pdf



Note: * To enter and exit standby mode without any external stimulus on PUB or TRST, the *vr_en_mat* in the CTRL_STAT register must also be set to 1, so that RTCPSMMATCH will assert when a match occurs; hence the device exits standby mode.

Figure 2-31 • State Diagram for All Different Power Modes

When TRST is 1 or PUB is 0, the 1.5 V voltage regulator is always ON, putting the Fusion device in normal operation at all times. Therefore, when the JTAG port is not in reset, the Fusion device cannot enter sleep mode or standby mode.

To enter standby mode, the Fusion device must first power-up into normal operation. The RTC is enabled through the RTC Control/Status Register described in the "Real-Time Counter (part of AB macro)" section on page 2-33. A match value corresponding to the wake-up time is loaded into the Match Register. The 1.5 V voltage regulator is disabled by setting VRPU to 0 to allow the Fusion device to enter standby mode, when the 1.5 V supply is off but the RTC remains on.

Flash Memory Block Diagram

A simplified diagram of the flash memory block is shown in Figure 2-33.

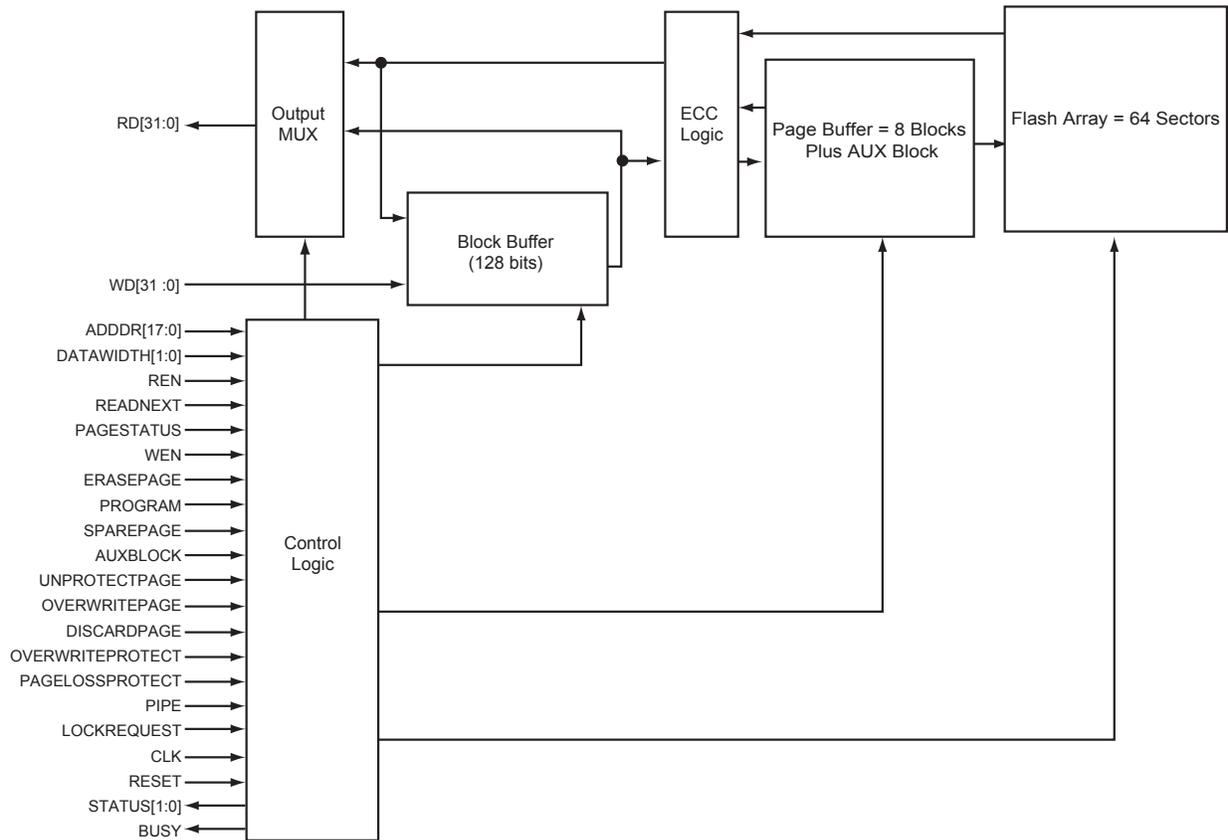


Figure 2-33 • Flash Memory Block Diagram

The logic consists of the following sub-blocks:

- Flash Array
Contains all stored data. The flash array contains 64 sectors, and each sector contains 33 pages of data.
- Page Buffer
A page-wide volatile register. A page contains 8 blocks of data and an AUX block.
- Block Buffer
Contains the contents of the last block accessed. A block contains 128 data bits.
- ECC Logic

The FB stores error correction information with each block to perform single-bit error correction and double-bit error detection on all data blocks.

Read Operation

Read operations are designed to read data from the FB Array, Page Buffer, Block Buffer, or status registers. Read operations support a normal read and a read-ahead mode (done by asserting READNEXT). Also, the timing for Read operations is dependent on the setting of PIPE.

The following diagrams illustrate representative timing for Non-Pipe Mode (Figure 2-38) and Pipe Mode (Figure 2-39) reads of the flash memory block interface.

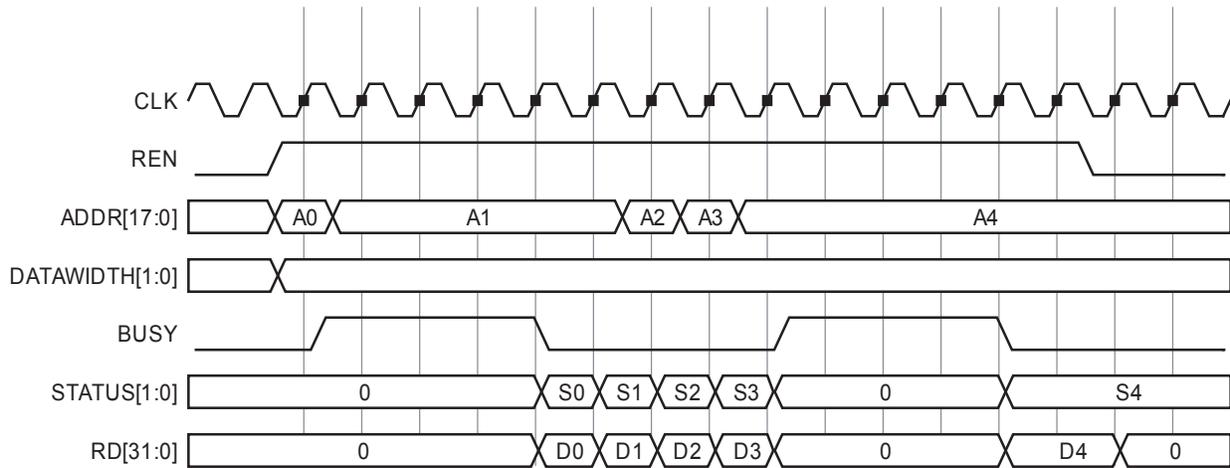


Figure 2-38 • Read Waveform (Non-Pipe Mode, 32-bit access)

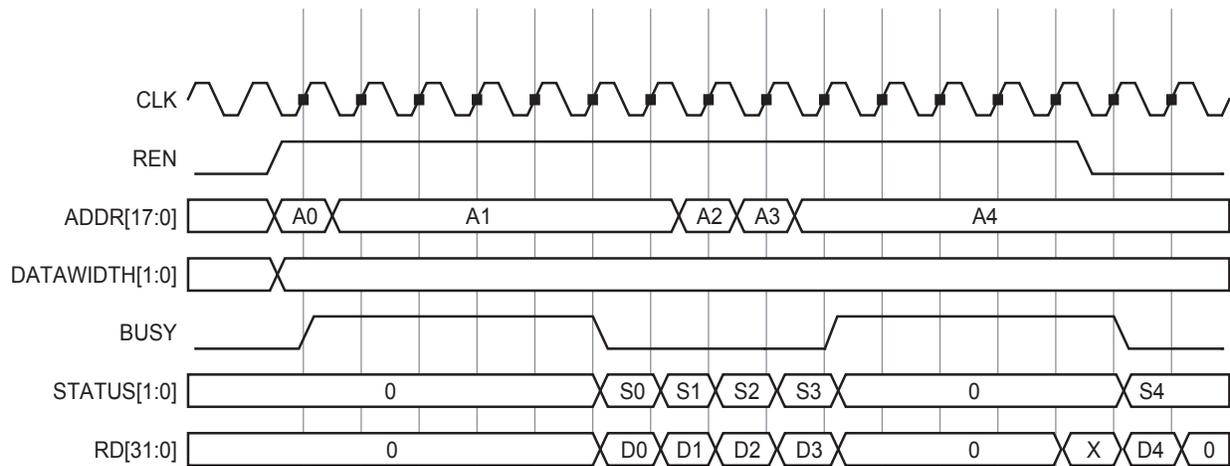


Figure 2-39 • Read Waveform (Pipe Mode, 32-bit access)

The AEMPTY flag is asserted when the difference between the write address and the read address is less than a predefined value. In the example above, a value of 200 for AEVAL means that the AEMPTY flag will be asserted when a read causes the difference between the write address and the read address to drop to 200. It will stay asserted until that difference rises above 200. Note that the FIFO can be configured with different read and write widths; in this case, the AFVAL setting is based on the number of write data entries and the AEVAL setting is based on the number of read data entries. For aspect ratios of 512×9 and 256×18, only 4,096 bits can be addressed by the 12 bits of AFVAL and AEVAL. The number of words must be multiplied by 8 and 16, instead of 9 and 18. The SmartGen tool automatically uses the proper values. To avoid halfwords being written or read, which could happen if different read and write aspect ratios are specified, the FIFO will assert FULL or EMPTY as soon as at least a minimum of one word cannot be written or read. For example, if a two-bit word is written and a four-bit word is being read, the FIFO will remain in the empty state when the first word is written. This occurs even if the FIFO is not completely empty, because in this case, a complete word cannot be read. The same is applicable in the full state. If a four-bit word is written and a two-bit word is read, the FIFO is full and one word is read. The FULL flag will remain asserted because a complete word cannot be written at this point.

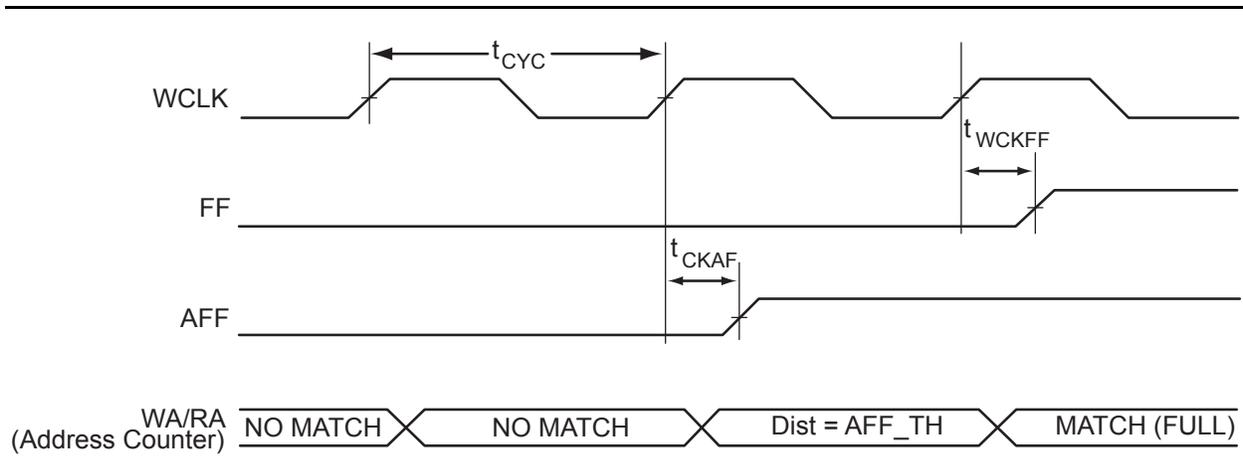


Figure 2-61 • FIFO FULL and AFULL Flag Assertion

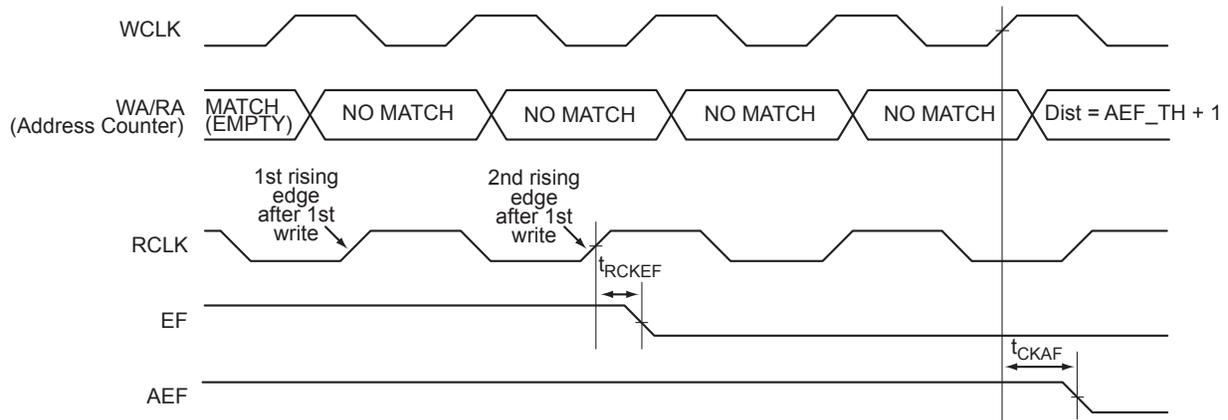


Figure 2-62 • FIFO EMPTY Flag and AEMPTY Flag Deassertion

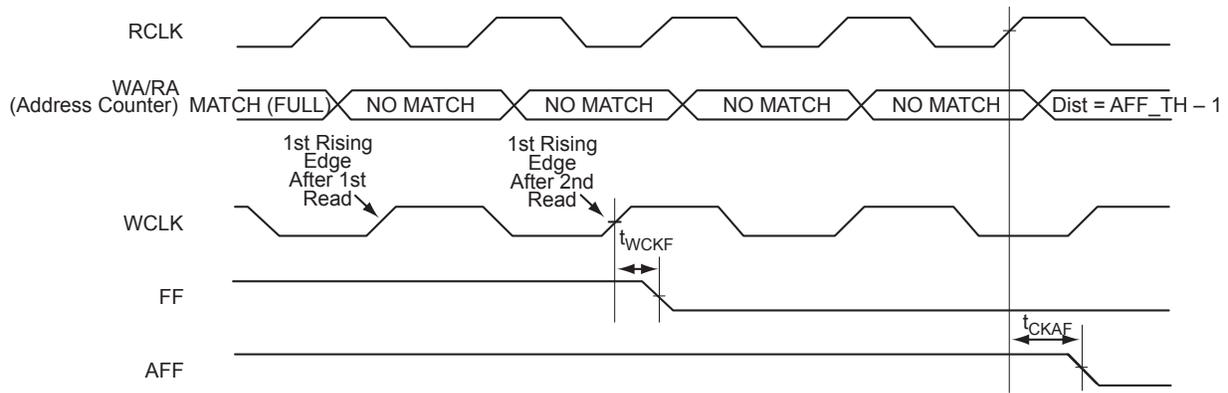


Figure 2-63 • FIFO FULL Flag and AFULL Flag Deassertion

Voltage Monitor

The Fusion Analog Quad offers a robust set of voltage-monitoring capabilities unique in the FPGA industry. The Analog Quad comprises three analog input pads— Analog Voltage (AV), Analog Current (AC), and Analog Temperature (AT)—and a single gate driver output pad, Analog Gate (AG). There are many common characteristics among the analog input pads. Each analog input can be configured to connect directly to the input MUX of the ADC. When configured in this manner (Figure 2-66), there will be no prescaling of the input signal. Care must be taken in this mode not to drive the ADC into saturation by applying an input voltage greater than the reference voltage. The internal reference voltage of the ADC is 2.56 V. Optionally, an external reference can be supplied by the user. The external reference can be a maximum of 3.3 V DC.

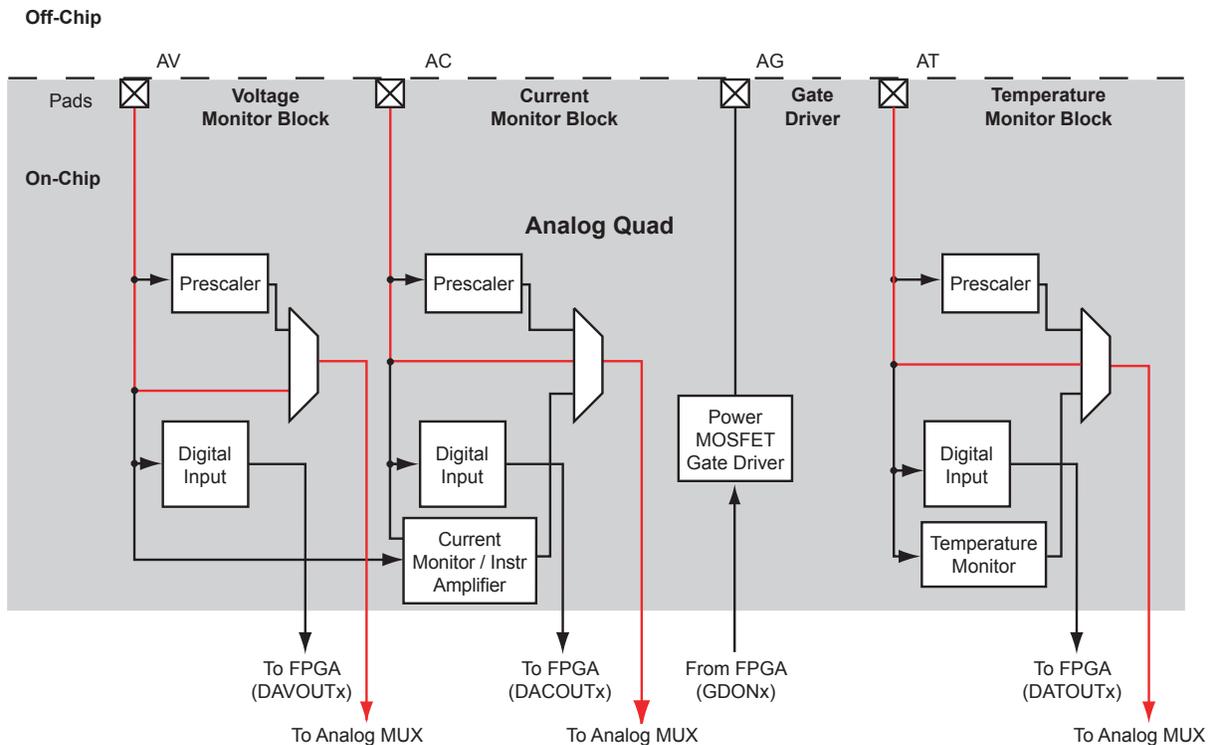
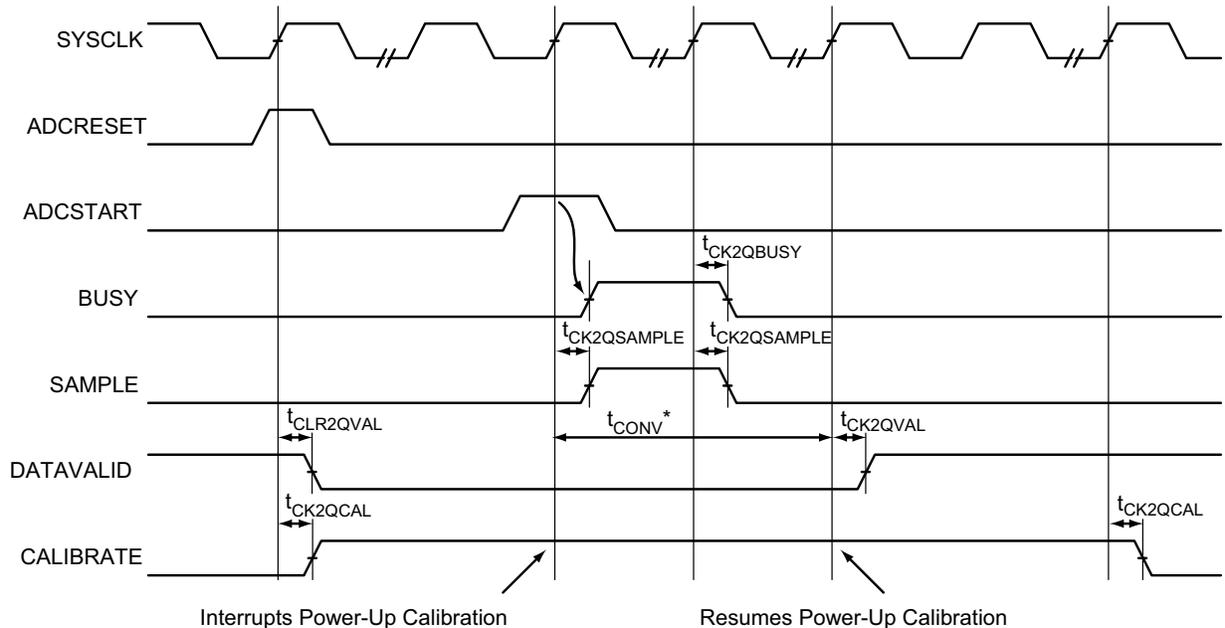


Figure 2-66 • Analog Quad Direct Connect

The Analog Quad offers a wide variety of prescaling options to enable the ADC to resolve the input signals. Figure 2-67 shows the path through the Analog Quad for a signal that is to be prescaled prior to conversion. The ADC internal reference voltage and the prescaler factors were selected to make both prescaling and postsaling of the signals easy binary calculations (refer to Table 2-57 on page 2-130 for details). When an analog input pad is configured with a prescaler, there will be a 1 M Ω resistor to ground. This occurs even when the device is in power-down mode. In low power standby or sleep mode (VCC is OFF, VCC33A is ON, VCCI is ON) or when the resource is not used, analog inputs are pulled down to ground through a 1 M Ω resistor. The gate driver output is floating (or tristated), and there is no extra current on VCC33A.

These scaling factors hold true whether the particular pad is configured to accept a positive or negative voltage. Note that whereas the AV and AC pads support the same prescaling factors, the AT pad supports a reduced set of prescaling factors and supports positive voltages only.

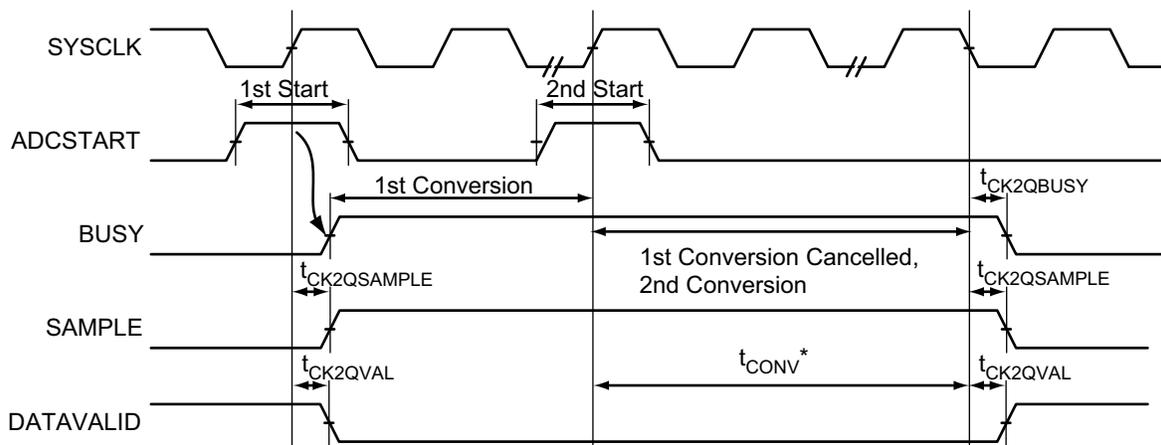
Intra-Conversion



Note: t_{CONV}^* represents the conversion time of the second conversion. See EQ 23 on page 2-109 for calculation of the conversion time, t_{CONV} .

Figure 2-92 • Intra-Conversion Timing Diagram

Injected Conversion



Note: *See EQ 23 on page 2-109 for calculation on the conversion time, t_{CONV} .

Figure 2-93 • Injected Conversion Timing Diagram

Table 2-83 • Fusion Pro I/O Supported Standards and Corresponding VREF and VTT Voltages

I/O Standard	Input/Output Supply Voltage (VCCI_TYP)	Input Reference Voltage (VREF_TYP)	Board Termination Voltage (VTT_TYP)
LVTTTL/LVCMOS 3.3 V	3.30 V	–	–
LVC MOS 2.5 V	2.50 V	–	–
LVC MOS 2.5 V / 5.0 V Input	2.50 V	–	–
LVC MOS 1.8 V	1.80 V	–	–
LVC MOS 1.5 V	1.50 V	–	–
PCI 3.3 V	3.30 V	–	–
PCI-X 3.3 V	3.30 V	–	–
GTL+ 3.3 V	3.30 V	1.00 V	1.50 V
GTL+ 2.5 V	2.50 V	1.00 V	1.50 V
GTL 3.3 V	3.30 V	0.80 V	1.20 V
GTL 2.5 V	2.50 V	0.80 V	1.20 V
HSTL Class I	1.50 V	0.75 V	0.75 V
HSTL Class II	1.50 V	0.75 V	0.75 V
SSTL3 Class I	3.30 V	1.50 V	1.50 V
SSTL3 Class II	3.30 V	1.50 V	1.50 V
SSTL2 Class I	2.50 V	1.25 V	1.25 V
SSTL2 Class II	2.50 V	1.25 V	1.25 V
LVDS, BLVDS, M-LVDS	2.50 V	–	–
LVPECL	3.30 V	–	–

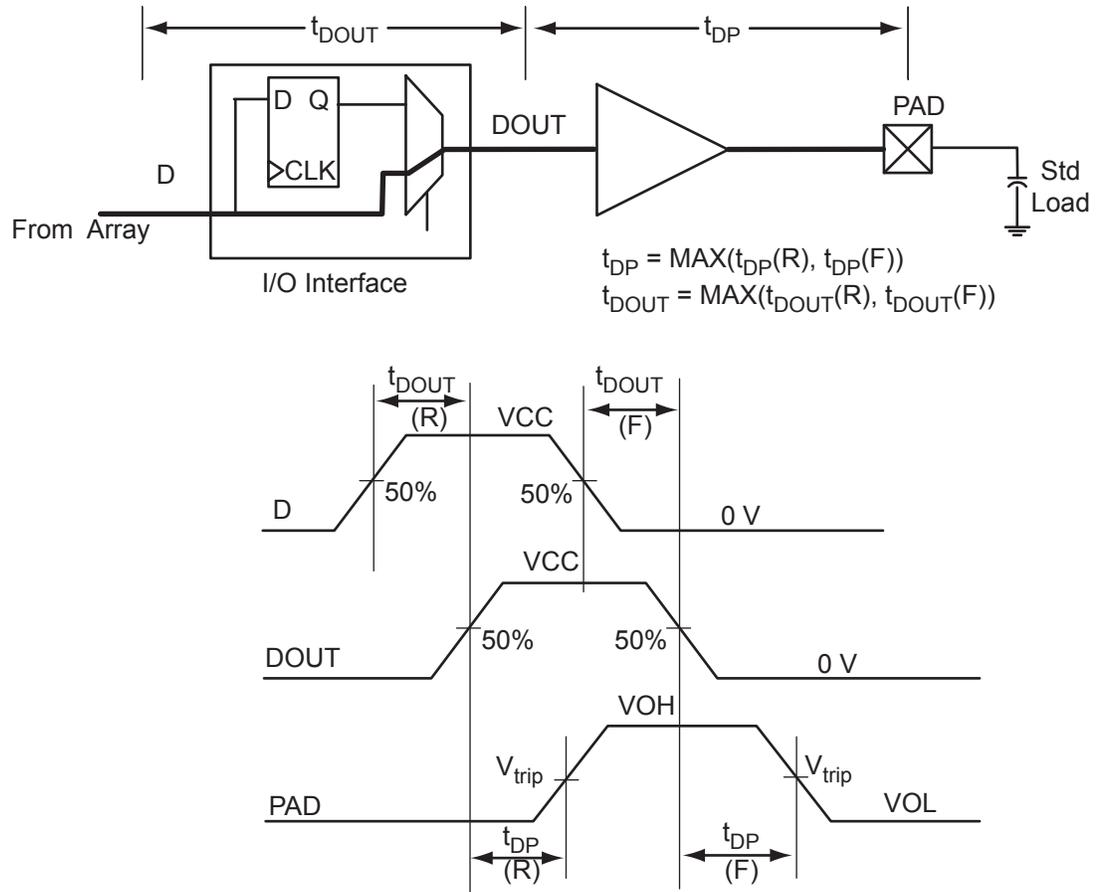


Figure 2-117 • Output Buffer Model and Delays (example)

Table 2-115 • 2.5 V LVC MOS High Slew
Commercial Temperature Range Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$,
Worst-Case $V_{CCI} = 2.3\text{ V}$
Applicable to Advanced I/Os

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	8.66	0.04	1.31	0.43	7.83	8.66	2.68	2.30	10.07	10.90	ns
	-1	0.56	7.37	0.04	1.11	0.36	6.66	7.37	2.28	1.96	8.56	9.27	ns
	-2	0.49	6.47	0.03	0.98	0.32	5.85	6.47	2.00	1.72	7.52	8.14	ns
8 mA	Std.	0.66	5.17	0.04	1.31	0.43	5.04	5.17	3.05	3.00	7.27	7.40	ns
	-1	0.56	4.39	0.04	1.11	0.36	4.28	4.39	2.59	2.55	6.19	6.30	ns
	-2	0.49	3.86	0.03	0.98	0.32	3.76	3.86	2.28	2.24	5.43	5.53	ns
12 mA	Std.	0.66	3.56	0.04	1.31	0.43	3.63	3.43	3.30	3.44	5.86	5.67	ns
	-1	0.56	3.03	0.04	1.11	0.36	3.08	2.92	2.81	2.92	4.99	4.82	ns
	-2	0.49	2.66	0.03	0.98	0.32	2.71	2.56	2.47	2.57	4.38	4.23	ns
16 mA	Std.	0.66	3.35	0.04	1.31	0.43	3.41	3.06	3.36	3.55	5.65	5.30	ns
	-1	0.56	2.85	0.04	1.11	0.36	2.90	2.60	2.86	3.02	4.81	4.51	ns
	-2	0.49	2.50	0.03	0.98	0.32	2.55	2.29	2.51	2.65	4.22	3.96	ns
24 mA	Std.	0.66	3.56	0.04	1.31	0.43	3.63	3.43	3.30	3.44	5.86	5.67	ns
	-1	0.56	3.03	0.04	1.11	0.36	3.08	2.92	2.81	2.92	4.99	4.82	ns
	-2	0.49	2.66	0.03	0.98	0.32	2.71	2.56	2.47	2.57	4.38	4.23	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to [Table 3-7](#) on [page 3-9](#).

Table 2-116 • 2.5 V LVC MOS Low Slew
Commercial Temperature Range Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$,
Worst-Case $V_{CCI} = 2.3\text{ V}$
Applicable to Standard I/Os

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	11.00	0.04	1.29	0.43	10.37	11.00	2.03	1.83	ns
	-1	0.56	9.35	0.04	1.10	0.36	8.83	9.35	1.73	1.56	ns
	-2	0.49	8.21	0.03	0.96	0.32	7.75	8.21	1.52	1.37	ns
4 mA	Std.	0.66	11.00	0.04	1.29	0.43	10.37	11.00	2.03	1.83	ns
	-1	0.56	9.35	0.04	1.10	0.36	8.83	9.35	1.73	1.56	ns
	-2	0.49	8.21	0.03	0.96	0.32	7.75	8.21	1.52	1.37	ns
6 mA	Std.	0.66	7.50	0.04	1.29	0.43	7.36	7.50	2.39	2.46	ns
	-1	0.56	6.38	0.04	1.10	0.36	6.26	6.38	2.03	2.10	ns
	-2	0.49	5.60	0.03	0.96	0.32	5.49	5.60	1.78	1.84	ns
8 mA	Std.	0.66	7.50	0.04	1.29	0.43	7.36	7.50	2.39	2.46	ns
	-1	0.56	6.38	0.04	1.10	0.36	6.26	6.38	2.03	2.10	ns
	-2	0.49	5.60	0.03	0.96	0.32	5.49	5.60	1.78	1.84	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to [Table 3-7](#) on [page 3-9](#).

3.3 V GTL+

Gunning Transceiver Logic Plus is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 3.3 V.

Table 2-144 • Minimum and Maximum DC Input and Output Levels

3.3 V GTL+	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	mA ³	mA ³	μA ⁴	μA ⁴
35 mA	-0.3	VREF - 0.1	VREF + 0.1	3.6	0.6	-	35	35	181	268	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.

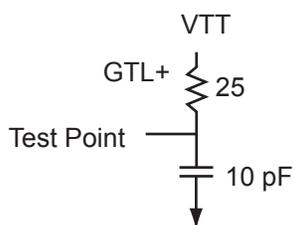


Figure 2-126 • AC Loading

Table 2-145 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF - 0.1	VREF + 0.1	1.0	1.0	1.5	10

Note: *Measuring point = Vtrip. See Table 2-90 on page 2-166 for a complete table of trip points.

Timing Characteristics

Table 2-146 • 3.3 V GTL+

Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 3.0 V, VREF = 1.0 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
Std.	0.66	2.06	0.04	1.59	0.43	2.09	2.06			4.33	4.29	ns
-1	0.56	1.75	0.04	1.35	0.36	1.78	1.75			3.68	3.65	ns
-2	0.49	1.53	0.03	1.19	0.32	1.56	1.53			3.23	3.20	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.

Table 2-174 • Parameter Definitions and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t _{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t _{OSUD}	Data Setup Time for the Output Data Register	F, H
t _{OHD}	Data Hold Time for the Output Data Register	F, H
t _{OSUE}	Enable Setup Time for the Output Data Register	G, H
t _{OHE}	Enable Hold Time for the Output Data Register	G, H
t _{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
t _{OREMPRE}	Asynchronous Preset Removal Time for the Output Data Register	L, H
t _{ORECPRE}	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t _{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t _{OESUD}	Data Setup Time for the Output Enable Register	J, H
t _{OEHD}	Data Hold Time for the Output Enable Register	J, H
t _{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t _{OEHE}	Enable Hold Time for the Output Enable Register	K, H
t _{OEPRE2Q}	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
t _{OEREMPRE}	Asynchronous Preset Removal Time for the Output Enable Register	I, H
t _{OERECPRE}	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t _{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t _{ISUD}	Data Setup Time for the Input Data Register	C, A
t _{IHD}	Data Hold Time for the Input Data Register	C, A
t _{ISUE}	Enable Setup Time for the Input Data Register	B, A
t _{IHE}	Enable Hold Time for the Input Data Register	B, A
t _{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
t _{IEMPRE}	Asynchronous Preset Removal Time for the Input Data Register	D, A
t _{IRECPRE}	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-137 on page 2-212 for more information.

Output Register

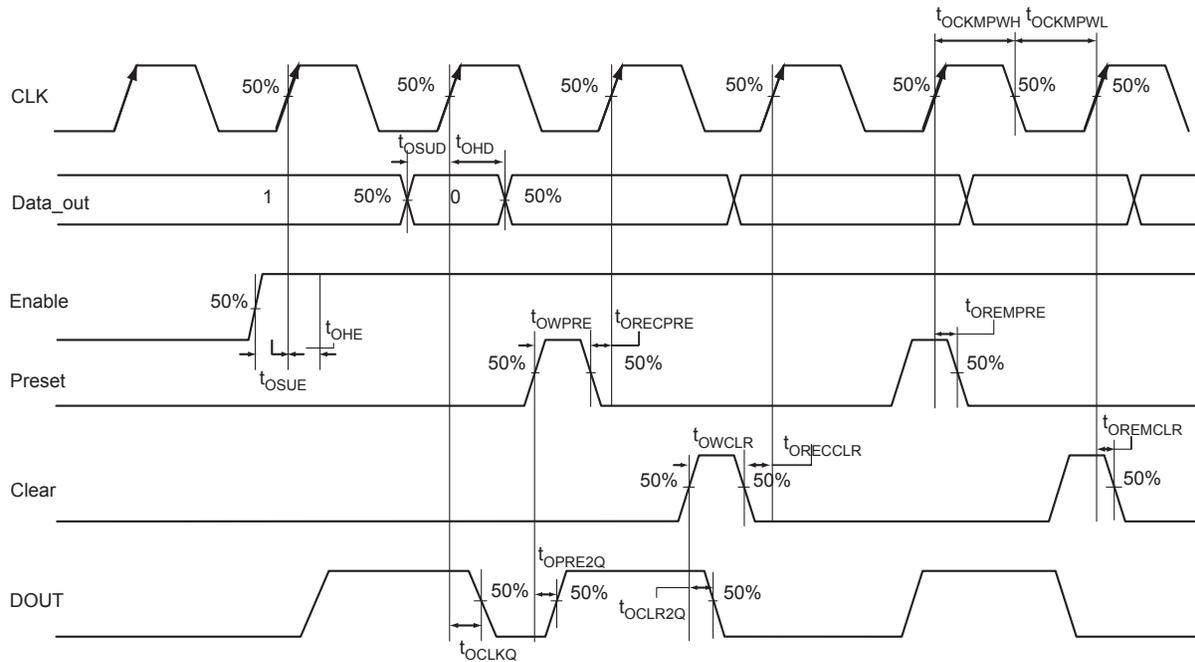


Figure 2-140 • Output Register Timing Diagram

Timing Characteristics

Table 2-177 • Output Data Register Propagation Delays
Commercial Temperature Range Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	0.59	0.67	0.79	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.31	0.36	0.42	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	0.00	0.00	ns
t_{OSUE}	Enable Setup Time for the Output Data Register	0.44	0.50	0.59	ns
t_{OHE}	Enable Hold Time for the Output Data Register	0.00	0.00	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	0.80	0.91	1.07	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	0.80	0.91	1.07	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	0.00	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.22	0.25	0.30	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	0.00	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.22	0.25	0.30	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.22	0.25	0.30	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.22	0.25	0.30	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.36	0.41	0.48	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.32	0.37	0.43	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to [Table 3-7](#) on [page 3-9](#).

ATRTNx Temperature Monitor Return

AT returns are the returns for the temperature sensors. The cathode terminal of the external diodes should be connected to these pins. There is one analog return pin for every two Analog Quads. The x in the ATRTNx designator indicates the quad pairing (x = 0 for AQ1 and AQ2, x = 1 for AQ2 and AQ3, ..., x = 4 for AQ8 and AQ9). The signals that drive these pins are called out as ATRETURNxy in the software (where x and y refer to the quads that share the return signal). ATRTN is internally connected to ground. It can be left floating when it is unused. The maximum capacitance allowed across the AT pins is 500 pF.

GL Globals

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as Pro I/Os since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors. See more detailed descriptions of global I/O connectivity in the "[Clock Conditioning Circuits](#)" section on page 2-22.

Refer to the "[User I/O Naming Convention](#)" section on page 2-158 for a description of naming of global pins.

JTAG Pins

Fusion devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the Fusion part must be supplied to allow JTAG signals to transition the Fusion device.

Isolating the JTAG power supply in a separate I/O bank gives greater flexibility with supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned to be used, the VJTAG pin together with the TRST pin could be tied to GND.

TCK Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND or VJTAG through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 Ω to 1 k Ω will satisfy the requirements. Refer to [Table 2-183](#) for more information.

Table 2-183 • Recommended Tie-Off Values for the TCK and TRST Pins

VJTAG	Tie-Off Resistance ^{2, 3}
VJTAG at 3.3 V	200 Ω to 1 k Ω
VJTAG at 2.5 V	200 Ω to 1 k Ω
VJTAG at 1.8 V	500 Ω to 1 k Ω
VJTAG at 1.5 V	500 Ω to 1 k Ω

Notes:

1. Equivalent parallel resistance if more than one device is on JTAG chain.
2. The TCK pin can be pulled up/down.
3. The TRST pin can only be pulled down.

TDI Test Data Input

Serial input for JTAG boundary scan, ISP, and UJTAG usage. There is an internal weak pull-up resistor on the TDI pin.

TDO Test Data Output

Serial output for JTAG boundary scan, ISP, and UJTAG usage.

Table 3-2 • Recommended Operating Conditions¹

Symbol	Parameter ²	Commercial	Industrial	Units	
T _J	Junction temperature	0 to +85	-40 to +100	°C	
VCC	1.5 V DC core supply voltage	1.425 to 1.575	1.425 to 1.575	V	
VJTAG	JTAG DC voltage	1.4 to 3.6	1.4 to 3.6	V	
VPUMP	Programming voltage	Programming mode ³	3.15 to 3.45	3.15 to 3.45	V
		Operation ⁴	0 to 3.6	0 to 3.6	V
VCCPLL	Analog power supply (PLL)	1.425 to 1.575	1.425 to 1.575	V	
VCCI	1.5 V DC supply voltage	1.425 to 1.575	1.425 to 1.575	V	
	1.8 V DC supply voltage	1.7 to 1.9	1.7 to 1.9	V	
	2.5 V DC supply voltage	2.3 to 2.7	2.3 to 2.7	V	
	3.3 V DC supply voltage	3.0 to 3.6	3.0 to 3.6	V	
	LVDS differential I/O	2.375 to 2.625	2.375 to 2.625	V	
	LVPECL differential I/O	3.0 to 3.6	3.0 to 3.6	V	
VCC33A	+3.3 V power supply	2.97 to 3.63	2.97 to 3.63	V	
VCC33PMP	+3.3 V power supply	2.97 to 3.63	2.97 to 3.63	V	
VAREF	Voltage reference for ADC	2.527 to 2.593	2.527 to 2.593	V	
VCC15A ⁵	Digital power supply for the analog system	1.425 to 1.575	1.425 to 1.575	V	
VCCNVM	Embedded flash power supply	1.425 to 1.575	1.425 to 1.575	V	
VCCOSC	Oscillator power supply	2.97 to 3.63	2.97 to 3.63	V	
AV, AC ⁶	Unpowered, ADC reset asserted or unconfigured	-10.5 to 12.0	-10.5 to 11.6	V	
	Analog input (+16 V to +2 V prescaler range)	-0.3 to 12.0	-0.3 to 11.6	V	
	Analog input (+1 V to +0.125 V prescaler range)	-0.3 to 3.6	-0.3 to 3.6	V	
	Analog input (-16 V to -2 V prescaler range)	-10.5 to 0.3	-10.5 to 0.3	V	
	Analog input (-1 V to -0.125 V prescaler range)	-3.6 to 0.3	-3.6 to 0.3	V	
	Analog input (direct input to ADC)	-0.3 to 3.6	-0.3 to 3.6	V	
	Digital input	-0.3 to 12.0	-0.3 to 11.6	V	
AG ⁶	Unpowered, ADC reset asserted or unconfigured	-10.5 to 12.0	-10.5 to 11.6	V	
	Low Current Mode (1 μA, 3 μA, 10 μA, 30 μA)	-0.3 to 12.0	-0.3 to 11.6	V	
	Low Current Mode (-1 μA, -3 μA, -10 μA, -30 μA)	-10.5 to 0.3	-10.5 to 0.3	V	
	High Current Mode ⁷	-10.5 to 12.0	-10.5 to 11.6	V	
AT ⁶	Unpowered, ADC reset asserted or unconfigured	-0.3 to 15.5	-0.3 to 14.5	V	
	Analog input (+16 V, +4 V prescaler range)	-0.3 to 15.5	-0.3 to 14.5	V	
	Analog input (direct input to ADC)	-0.3 to 3.6	-0.3 to 3.6	V	
	Digital input	-0.3 to 15.5	-0.3 to 14.5	V	

Notes:

1. The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in Table 2-85 on page 2-157.
2. All parameters representing voltages are measured with respect to GND unless otherwise specified.
3. The programming temperature range supported is $T_{\text{ambient}} = 0^{\circ}\text{C}$ to 85°C .
4. VPUMP can be left floating during normal operation (not programming mode).
5. Violating the V_{CC15A} recommended voltage supply during an embedded flash program cycle can corrupt the page being programmed.
6. The input voltage may overshoot by up to 500 mV above the Recommended Maximum (150 mV in Direct mode), provided the duration of the overshoot is less than 50% of the operating lifetime of the device.
7. The AG pad should also conform to the limits as specified in Table 2-48 on page 2-114.

Theta-JA

Junction-to-ambient thermal resistance (θ_{JA}) is determined under standard conditions specified by JEDEC (JESD-51), but it has little relevance in actual performance of the product. It should be used with caution but is useful for comparing the thermal performance of one package to another.

A sample calculation showing the maximum power dissipation allowed for the AFS600-FG484 package under forced convection of 1.0 m/s and 75°C ambient temperature is as follows:

$$\text{Maximum Power Allowed} = \frac{T_{J(\text{MAX})} - T_{A(\text{MAX})}}{\theta_{JA}}$$

EQ 4

where

$$\theta_{JA} = 19.00^{\circ}\text{C/W (taken from Table 3-6 on page 3-7).}$$

$$T_A = 75.00^{\circ}\text{C}$$

$$\text{Maximum Power Allowed} = \frac{100.00^{\circ}\text{C} - 75.00^{\circ}\text{C}}{19.00^{\circ}\text{C/W}} = 1.3 \text{ W}$$

EQ 5

The power consumption of a device can be calculated using the Microsemi power calculator. The device's power consumption must be lower than the calculated maximum power dissipation by the package. If the power consumption is higher than the device's maximum allowable power dissipation, a heat sink can be attached on top of the case, or the airflow inside the system must be increased.

Theta-JB

Junction-to-board thermal resistance (θ_{JB}) measures the ability of the package to dissipate heat from the surface of the chip to the PCB. As defined by the JEDEC (JESD-51) standard, the thermal resistance from junction to board uses an isothermal ring cold plate zone concept. The ring cold plate is simply a means to generate an isothermal boundary condition at the perimeter. The cold plate is mounted on a JEDEC standard board with a minimum distance of 5.0 mm away from the package edge.

Theta-JC

Junction-to-case thermal resistance (θ_{JC}) measures the ability of a device to dissipate heat from the surface of the chip to the top or bottom surface of the package. It is applicable for packages used with external heat sinks. Constant temperature is applied to the surface in consideration and acts as a boundary condition. This only applies to situations where all or nearly all of the heat is dissipated through the surface in consideration.

Calculation for Heat Sink

For example, in a design implemented in an AFS600-FG484 package with 2.5 m/s airflow, the power consumption value using the power calculator is 3.00 W. The user-dependent T_a and T_j are given as follows:

$$T_J = 100.00^{\circ}\text{C}$$

$$T_A = 70.00^{\circ}\text{C}$$

From the datasheet:

$$\theta_{JA} = 17.00^{\circ}\text{C/W}$$

$$\theta_{JC} = 8.28^{\circ}\text{C/W}$$

$$P = \frac{T_J - T_A}{\theta_{JA}} = \frac{100^{\circ}\text{C} - 70^{\circ}\text{C}}{17.00 \text{ W}} = 1.76 \text{ W}$$

EQ 6

RC Oscillator Dynamic Contribution— P_{RC-OSC}

Operating Mode

$$P_{RC-OSC} = PAC19$$

Standby Mode and Sleep Mode

$$P_{RC-OSC} = 0 \text{ W}$$

Analog System Dynamic Contribution— P_{AB}

Operating Mode

$$P_{AB} = PAC20$$

Standby Mode and Sleep Mode

$$P_{AB} = 0 \text{ W}$$

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that the net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100%, as all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
 - Bit 0 (LSB) = 100%
 - Bit 1 = 50%
 - Bit 2 = 25%
 - ...
 - Bit 7 (MSB) = 0.78125%
 - Average toggle rate = $(100\% + 50\% + 25\% + 12.5\% + \dots + 0.78125\%) / 8$.

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When non-tristate output buffers are used, the enable rate should be 100%.

Table 3-16 • Toggle Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

Table 3-17 • Enable Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%
β_4	NVM enable rate for read operations	0%

FG256				
Pin Number	AFS090 Function	AFS250 Function	AFS600 Function	AFS1500 Function
E13	VCCIB1	VCCIB1	VCCIB2	VCCIB2
E14	GCC2/IO33NDB1V0	IO42NDB1V0	IO32NDB2V0	IO46NDB2V0
E15	GCB2/IO33PDB1V0	GBC2/IO42PDB1V0	GBC2/IO32PDB2V0	GBC2/IO46PDB2V0
E16	GND	GND	GND	GND
F1	NC	NC	IO79NDB4V0	IO111NDB4V0
F2	NC	NC	IO79PDB4V0	IO111PDB4V0
F3	GFB1/IO48PPB3V0	IO72NDB3V0	IO76NDB4V0	IO112NDB4V0
F4	GFC0/IO49NDB3V0	IO72PDB3V0	IO76PDB4V0	IO112PDB4V0
F5	NC	NC	IO82PSB4V0	IO120PSB4V0
F6	GFC1/IO49PDB3V0	GAC2/IO74PPB3V0	GAC2/IO83PPB4V0	GAC2/IO123PPB4V0
F7	NC	IO09RSB0V0	IO04PPB0V0	IO05PPB0V1
F8	NC	IO19RSB0V0	IO08NDB0V1	IO11NDB0V1
F9	NC	NC	IO20PDB1V0	IO27PDB1V1
F10	NC	IO29RSB0V0	IO23NDB1V1	IO37NDB1V2
F11	NC	IO43NDB1V0	IO36NDB2V0	IO50NDB2V0
F12	NC	IO43PDB1V0	IO36PDB2V0	IO50PDB2V0
F13	NC	IO44NDB1V0	IO39NDB2V0	IO59NDB2V0
F14	NC	GCA2/IO44PDB1V0	GCA2/IO39PDB2V0	GCA2/IO59PDB2V0
F15	GCC1/IO34PDB1V0	GCB2/IO45PDB1V0	GCB2/IO40PDB2V0	GCB2/IO60PDB2V0
F16	GCC0/IO34NDB1V0	IO45NDB1V0	IO40NDB2V0	IO60NDB2V0
G1	GEC0/IO46NPB3V0	IO70NPB3V0	IO74NPB4V0	IO109NPB4V0
G2	VCCIB3	VCCIB3	VCCIB4	VCCIB4
G3	GEC1/IO46PPB3V0	GFB2/IO70PPB3V0	GFB2/IO74PPB4V0	GFB2/IO109PPB4V0
G4	GFA1/IO47PDB3V0	GFA2/IO71PDB3V0	GFA2/IO75PDB4V0	GFA2/IO110PDB4V0
G5	GND	GND	GND	GND
G6	GFA0/IO47NDB3V0	IO71NDB3V0	IO75NDB4V0	IO110NDB4V0
G7	GND	GND	GND	GND
G8	VCC	VCC	VCC	VCC
G9	GND	GND	GND	GND
G10	VCC	VCC	VCC	VCC
G11	GDA1/IO37NDB1V0	GCC0/IO47NDB1V0	GCC0/IO43NDB2V0	GCC0/IO62NDB2V0
G12	GND	GND	GND	GND
G13	IO37PDB1V0	GCC1/IO47PDB1V0	GCC1/IO43PDB2V0	GCC1/IO62PDB2V0
G14	GCB0/IO35NPB1V0	IO46NPB1V0	IO41NPB2V0	IO61NPB2V0
G15	VCCIB1	VCCIB1	VCCIB2	VCCIB2
G16	GCB1/IO35PPB1V0	GCC2/IO46PPB1V0	GCC2/IO41PPB2V0	GCC2/IO61PPB2V0
H1	GEB1/IO45PDB3V0	GFC2/IO69PDB3V0	GFC2/IO73PDB4V0	GFC2/IO108PDB4V0
H2	GEB0/IO45NDB3V0	IO69NDB3V0	IO73NDB4V0	IO108NDB4V0

Revision	Changes	Page
Advance 1.0 (continued)	In Table 2-47 • ADC Characteristics in Direct Input Mode , the commercial conditions were updated and note 2 is new.	2-121
	The $V_{CC33ACAP}$ signal name was changed to "XTAL1 Crystal Oscillator Circuit Input".	2-228
	Table 2-48 • Uncalibrated Analog Channel Accuracy* is new.	2-123
	Table 2-49 • Calibrated Analog Channel Accuracy^{1,2,3} is new.	2-124
	Table 2-50 • Analog Channel Accuracy: Monitoring Standard Positive Voltages is new.	2-125
	In Table 2-57 • Voltage Polarity Control Truth Table—AV (x = 0), AC (x = 1), and AT (x = 3)* , the following I/O Bank names were changed: Hot-Swap changed to Standard LVDS changed to Advanced	2-131
	In Table 2-58 • Prescaler Op Amp Power-Down Truth Table—AV (x = 0), AC (x = 1), and AT (x = 3) , the following I/O Bank names were changed: Hot-Swap changed to Standard LVDS changed to Advanced	2-132
	In the title of Table 2-64 • I/O Standards Supported by Bank Type , LVDS I/O was changed to Advanced I/O.	2-134
	The title was changed from "Fusion Standard, LVDS, and Standard plus Hot-Swap I/O" to Table 2-68 • Fusion Standard and Advanced I/O Features . In addition, the table headings were all updated. The heading used to be Standard and LVDS I/O and was changed to Advanced I/O. Standard Hot-Swap was changed to just Standard.	2-136
	This sentence was deleted from the "Slew Rate Control and Drive Strength" section: The Standard hot-swap I/Os do not support slew rate control. In addition, these references were changed: • From: Fusion hot-swap I/O (Table 2-69 on page 2-122) To: Fusion Standard I/O • From: Fusion LVDS I/O (Table 2-70 on page 2-122) To: Fusion Advanced I/O	2-152
	The "Cold-Sparing Support" section was significantly updated.	2-143
	In the title of Table 2-75 • Fusion Standard I/O Standards—OUT_DRIVE Settings , Hot-Swap was changed to Standard.	2-153
	In the title of Table 2-76 • Fusion Advanced I/O Standards—SLEW and OUT_DRIVE Settings , LVDS was changed to Advanced.	2-153
	In the title of Table 2-81 • Fusion Standard and Advanced I/O Attributes vs. I/O Standard Applications , LVDS was changed to Advanced.	2-157
	In Figure 2-111 • Naming Conventions of Fusion Devices with Three Digital I/O Banks and Figure 2-112 • Naming Conventions of Fusion Devices with Four I/O Banks the following names were changed: Hot-Swap changed to Standard LVDS changed to Advanced	2-160
The Figure 2-113 • Timing Model was updated.	2-161	
In the notes for Table 2-86 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions , T_J was changed to T_A .	2-166	